

2SK3033 (Tentative)

Silicon N-Channel Power F-MOS FET

■ Features

- Avalanche energy capacity guaranteed
- High-speed switching
- Low ON-resistance
- No secondary breakdown
- Low-voltage drive
- High electrostatic breakdown voltage

■ Applications

- Contactless relay
- Diving circuit for a solenoid
- Driving circuit for a motor
- Control equipment
- Switching power supply

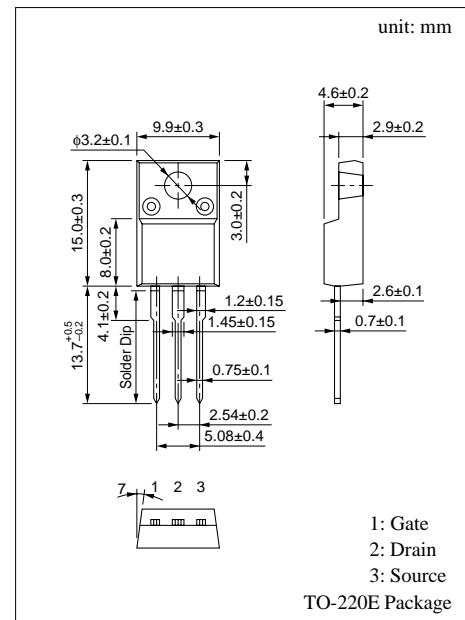
■ Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)

Parameter	Symbol	Rated	Unit	
Drain to Source breakdown voltage	V_{DSS}	100	V	
Gate to Source voltage	V_{GSS}	± 20	V	
Drain current	DC	I_D	± 40	A
	Pulse	I_{DP}	± 80	A
Avalanche energy capacity	EAS*	80	mJ	
Allowable power dissipation	$T_C = 25^\circ\text{C}$	P_D	60	W
	$T_a = 25^\circ\text{C}$		2	
Channel temperature	T_{ch}	150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	

* $L = 0.1\text{mH}$, $I_L = 40\text{A}$, 1 pulse

■ Electrical Characteristics ($T_C = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain to Source cut-off current	I_{DSS}	$V_{DS} = 80\text{V}$, $V_{GS} = 0$			10	μA	
Gate to Source leakage current	I_{GSS}	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0$			± 10	μA	
Drain to Source breakdown voltage	V_{DSS}	$I_D = 1\text{mA}$, $V_{GS} = 0$	100			V	
Gate threshold voltage	V_{th}	$V_{DS} = 10\text{V}$, $I_D = 1\text{mA}$	1		2.5	V	
Drain to Source ON-resistance	$R_{DS(on)1}$	$V_{GS} = 10\text{V}$, $I_D = 20\text{A}$		35	60	$\text{m}\Omega$	
	$R_{DS(on)2}$	$V_{GS} = 4\text{V}$, $I_D = 20\text{A}$		40	75	$\text{m}\Omega$	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}$, $I_D = 20\text{A}$	13	26		S	
Diode forward voltage	V_{DSF}	$I_{DR} = 20\text{A}$, $V_{GS} = 0$			-1.4	V	
Input capacitance (Common Source)	C_{iss}	$V_{DS} = 10\text{V}$, $V_{GS} = 0$, $f = 1\text{MHz}$		2400		pF	
Output capacitance (Common Source)	C_{oss}				530		pF
Reverse transfer capacitance (Common Source)	C_{rss}				220		pF
Turn-on time (delay time)	$t_{d(on)}$				12		ns
Rise time	t_r	$V_{DD} = 30\text{V}$, $I_D = 20\text{A}$ $V_{GS} = 10\text{V}$, $R_L = 1.5\Omega$		20		ns	
Fall time	t_f				120		ns
Turn-off time (delay time)	$t_{d(off)}$				600		ns
Thermal resistance between channel and case	$R_{th(ch-c)}$				2.08	$^\circ\text{C/W}$	
Thermal resistance between channel and atmosphere	$R_{th(ch-a)}$				62.5	$^\circ\text{C/W}$	



Internal Connection

